

GENERAL FEATURES

- $V_{DS} = 30V, I_D = 0.1A$

$$R_{DS(ON)} < 8\Omega @ V_{GS}=4V$$

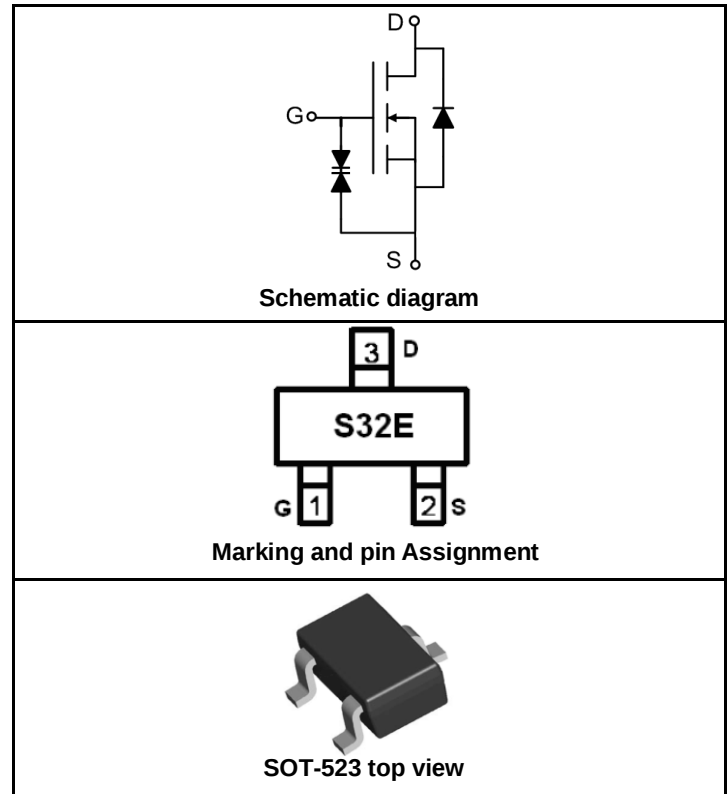
$$R_{DS(ON)} < 13\Omega @ V_{GS}=2.5V$$

ESD Rating: 1000V HBM

- High Power and current handling capability
- Lead free product is acquired
- Surface Mount Package

APPLICATION

- Direct Logic-Level Interface: TTL/CMOS
- Drivers: Relays, Solenoids, Lamps, Hammers, Display, Memories, Transistors, etc.
- Battery Operated Systems
- Solid-State Relays



PACKAGE MARKING AND ORDERING INFORMATION

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
S32E	SSF32E0E	SOT-523	Ø180mm	8 mm	3000 units

ABSOLUTE MAXIMUM RATINGS(TA=25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	±20	V
Drain Current-Continuous@ Current-Pulsed (Note 1)	I_D	0.1	A
	$I_D(70^\circ C)$	0.07	
	I_{DM}	0.4	A
Maximum Power Dissipation	P_D	0.2	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	°C

THERMAL CHARACTERISTICS

Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	400	°C/W
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ELECTRICAL CHARACTERISTICS (TA=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	30			V

Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =30V, V _{GS} =0V			1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±5V, V _{DS} =0V			100	nA
		V _{GS} =±10V, V _{DS} =0V			150	nA
		V _{GS} =±20V, V _{DS} =0V			10	uA
Gate-Source Breakdown Voltage	BV _{GSO}	V _{DS} =0V, I _G =±250uA	±20			V
ON CHARACTERISTICS (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	0.8		1.5	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =4V, I _D =0.01A		5	8	Ω
		V _{GS} =2.5V, I _D =0.001A		7	13	
Forward Transconductance	g _{FS}	V _{DS} =3V, I _D =0.01A	0.02			S
DYNAMIC CHARACTERISTICS (Note4)						
Input Capacitance	C _{ISS}	V _{DS} =5V, V _{GS} =0V, F=1.0MHz		45		PF
Output Capacitance	C _{OSS}			12		PF
Reverse Transfer Capacitance	C _{rSS}			7		PF
SWITCHING CHARACTERISTICS (Note 4)						
Turn-on Delay Time	t _{d(on)}	V _{DD} =5V, V _{GS} =5V, R _{GEN} =10Ω, R _L =500Ω I _D =0.01A		15		nS
Turn-Off Delay Time	t _{d(off)}			75		nS
DRAIN-SOURCE DIODE CHARACTERISTICS						
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V, I _S =0.01A			1.3	V

NOTES:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production testing.

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

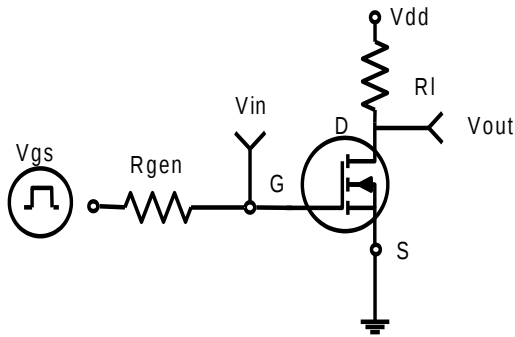


Figure 1: Switching Test Circuit

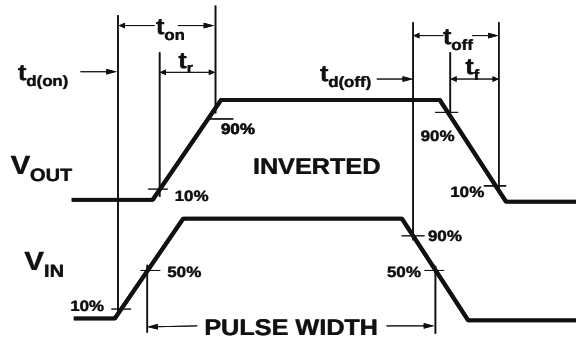


Figure 2: Switching Waveforms

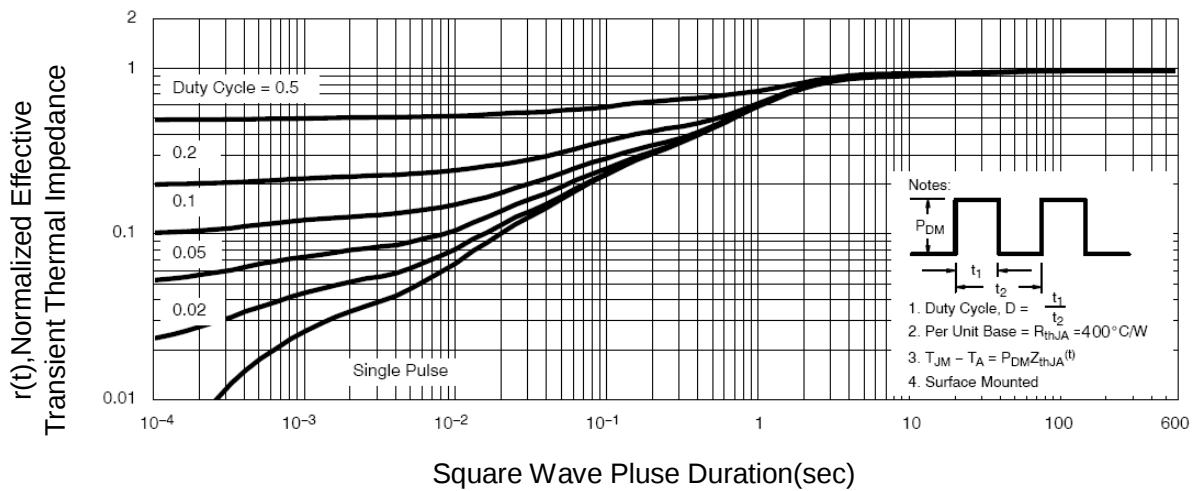
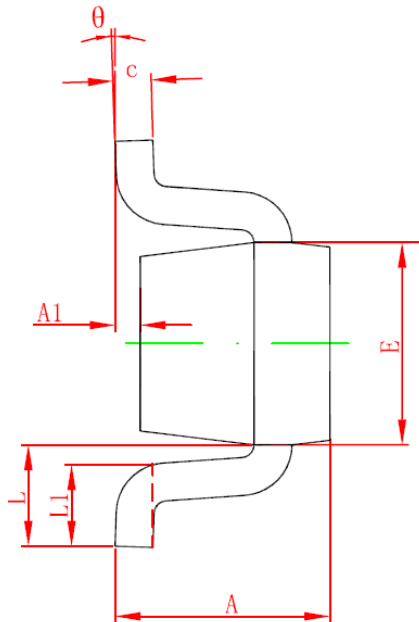
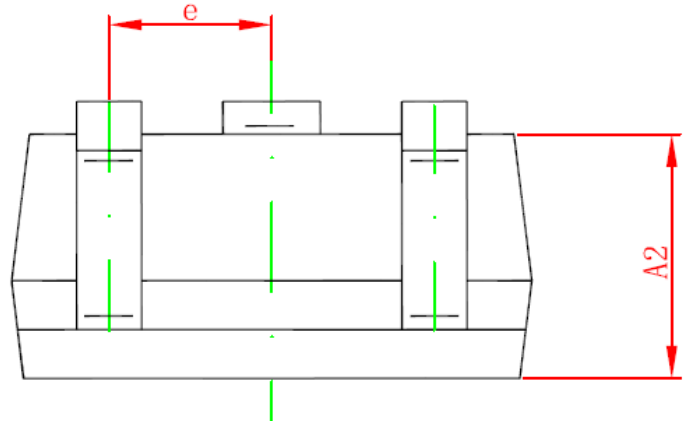
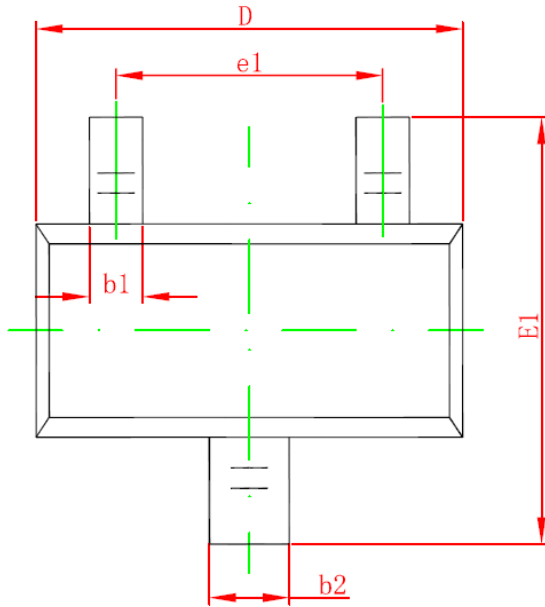


Figure 3 Normalized Maximum Transient Thermal Impedance

SOT-523 PACKAGE INFORMATION

Dimensions in Millimeters (UNIT:mm)



Symbol	Dimensions in Millimeters	
	MIN.	MAX.
A	0.700	0.900
A1	0.000	0.100
A2	0.700	0.800
b1	0.150	0.250
b2	0.250	0.350
c	0.100	0.200
D	1.500	1.700
E	0.700	0.900
E1	1.450	1.750
e	0.500TYP	
e1	0.900	1.100
L	0.400REF	
L1	0.260	0.460
theta	0°	8°

NOTES

1. All dimensions are in millimeters.
2. Tolerance $\pm 0.10\text{mm}$ (4 mil) unless otherwise specified
3. Package body sizes exclude mold flash and gate burrs. Mold flash at the non-lead sides should be less than 5 mils.
4. Dimension L is measured in gauge plane.
5. Controlling dimension is millimeter, converted inch dimensions are not necessarily exact.

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